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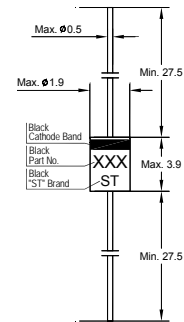
## 1SS106

### SILICON SCHOTTKY BARRIER DIODE

for various detector, high speed switching

#### Features

- Detection efficiency is very good.
- Small temperature coefficient.
- High reliability with glass seal.



Glass Case DO-35  
Dimensions in mm

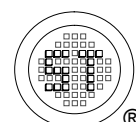
#### Absolute Maximum Ratings ( $T_a = 25\text{ }^\circ\text{C}$ )

Parameter	Symbol	Value	Unit
Reverse Voltage	$V_R$	10	V
Average Forward Current	$I_o$	30	mA
Junction Temperature	$T_J$	125	$^\circ\text{C}$
Storage Temperature Range	$T_{stg}$	- 55 to + 125	$^\circ\text{C}$

#### Electrical Characteristics at $T_a = 25\text{ }^\circ\text{C}$

Parameter	Symbol	Min.	Max.	Unit
Forward Current at $V_F = 1\text{ V}$	$I_F$	4.5	-	mA
Reverse Current at $V_R = 6\text{ V}$	$I_R$	-	70	$\mu\text{A}$
Capacitance at $V_R = 1\text{ V}$ , $f = 1\text{ MHz}$	C	-	1.5	pF
Rectifier Efficiency at $V_{in} = 2\text{ Vrms}$ , $f = 40\text{ MHz}$ , $R_L = 5\text{ K}\Omega$ , $C_L = 20\text{ pF}$	$\eta$	70	-	%
ESD Capability <sup>1)</sup> at $C = 200\text{ pF}$ , both forward and reverse direction 1 pulse.	-	100	-	V

<sup>1)</sup> Failure criterion:  $I_R \geq 140\text{ }\mu\text{A}$  at  $V_R = 6\text{ V}$



Dated : 20/06/2007